



Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

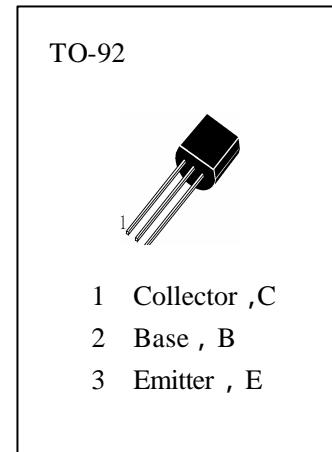
**H549**

## APPLICATIONS

Switching and Applications.

### ABSOLUTE MAXIMUM RATINGS ( $T_a=25$ )

$T_{stg}$	—Storage Temperature.....	-55~150
$T_j$	—Junction Temperature.....	150
$P_c$	—Collector Dissipation.....	500mW
$V_{CBO}$	—Collector-Base Voltage .....	30V
$V_{CEO}$	—Collector-Emitter Voltage.....	30V
$V_{EBO}$	—Emitter-Base Voltage.....	5V
$I_c$	—Collector Current.....	100mA



### ELECTRICAL CHARACTERISTICS ( $T_a=25$ )

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BVCBO	Collector-Base Breakdown Voltage	30			V	$I_C=100 \mu A, I_E=0$
BVCEO	Collector-Emitter Breakdown Voltage	30			V	$I_C=1mA, I_B=0$
BVEBO	Emitter-Base Breakdown Voltage	5			V	$I_E=1mA, I_C=0$
ICBO	Collector Cut-off Current			15	nA	$V_{CB}=30V, I_E=0$
HFE	DC Current Gain	110		800		$V_{CE}=5V, I_C=2mA$
VCE(sat1)	Collector- Emitter Saturation Voltage		90	250	mV	$I_C=10mA, I_B=0.5mA$
VCE(sat2)			200	600	mV	$I_C=100mA, I_B=5mA$
VBE(sat1)	Base-Emitter Saturation Voltage		0.7	1	V	$I_C=10mA, I_B=0.5mA$
VBE(sat2)			0.9	1.2	V	$I_C=100mA, I_B=5mA$
VBE(on)	Base-Emitter On Voltage	580	660	700	mV	$V_{CE}=5V, I_C=2mA$
f <sub>T</sub>	Current Gain-Bandwidth Product		300		MHz	$V_{CE}=5V, I_C=10mA$
C <sub>ob</sub>	Output Capacitance		2.5		pF	$V_{CB}=10V, I_E=0, f=1MHz$
NF	Noise Figure		1.2	4	dB	$V_{CE}=5V, I_C=0.2mA, f=1KHz, R_G=2K\Omega$

### $h_{FE}$ Classification

A

B

C

110—220

200—450

420—800



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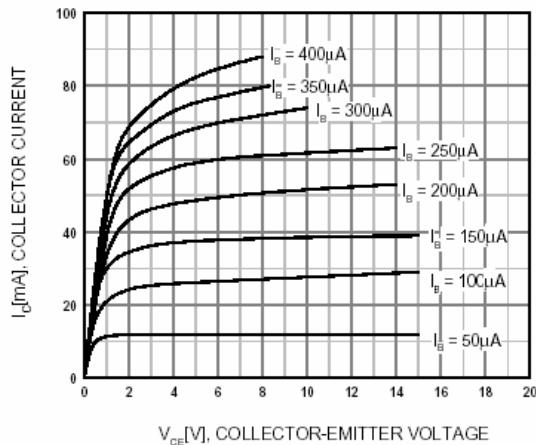


Figure 1. Static Characteristic

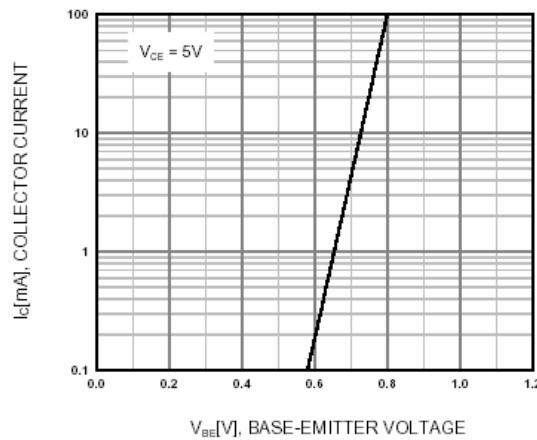


Figure 2. Transfer Characteristic

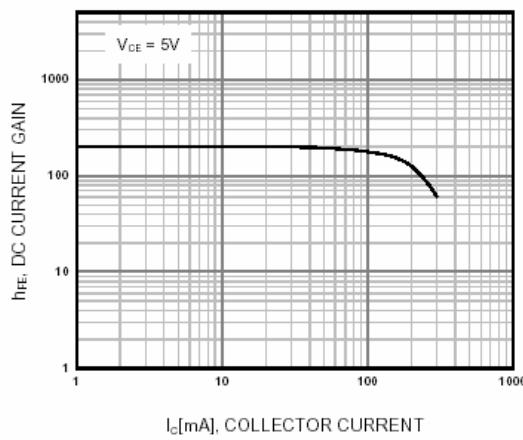


Figure 3. DC current Gain

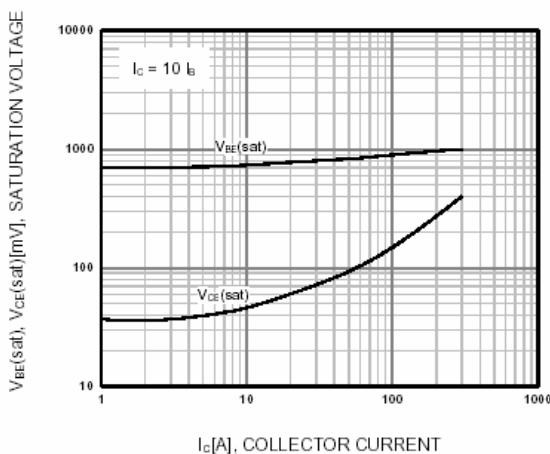


Figure 4. Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

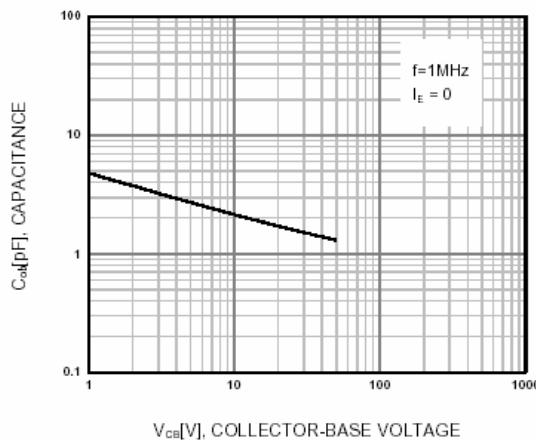


Figure 5. Output Capacitance

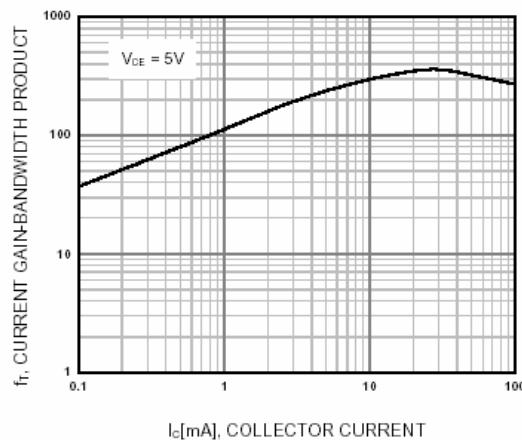


Figure 6. Current Gain Bandwidth Product